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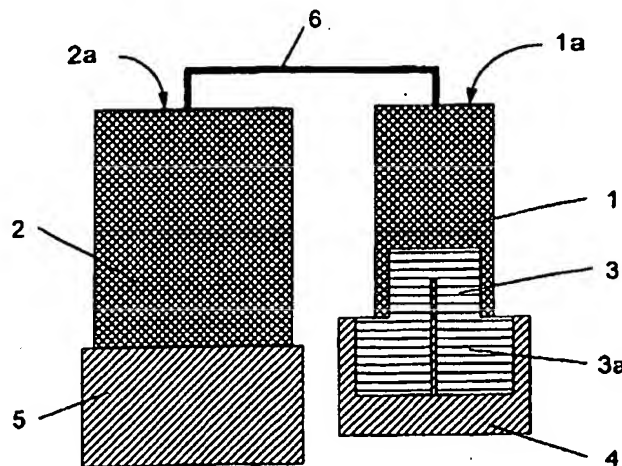
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(54) Title: A SENSOR COMPRISING MECHANICAL AMPLIFICATION OF SURFACE STRESS SENSITIVE CANTILEVER



(57) Abstract: The invention relates to a sensor comprising one or more sensor units, wherein at least one of the sensor units is in the form of a poly-cantilever structure. The poly-cantilever structure comprise two or more cantilever-like structures, at least one of the cantilever-like structures comprises a piezoresistive element, and at least one of the cantilever-like structures comprises a capture surface, at least one cantilever-like structure with a piezoresistive element designated a piezoresistive cantilever being connected in an amplifying connection to at least one of the cantilever-like structure with a capture surface designated a capture surface cantilever. The amplifying connection being provided so that a deflection of said capture surface cantilever due to a stress generated at said capture surface being capable of deflecting the connected piezoresistive cantilever. The sensor can be used for detection of a target substance in a fluid, such as a gas or a liquid.

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**A SENSOR COMPRISING MECHANICAL AMPLIFICATION OF A SURFACE
STRESS SENSITIVE CANTILEVER**

5 *Field of the invention*

The present invention relates to a sensor comprising one or more sensor units, wherein each sensor units comprises a capture surface area and a piezoresistive detection
10 system, for direct detection of stress change of the sensor unit. One type - the most commonly used type of sensor unit - is a cantilever.

Background of the invention

15 In the art of detecting components in fluids, cantilever based sensors with integrated piezoresistors are used as very sensitive mechanical stress sensors. As described in e.g. WO 0066266 and WO 9938007, micro cantilevers can be used for detection of molecular interaction. At least one
20 surface of the cantilever is coated with a capture layer, which capture layer reacts with a target molecule of interest. If the cantilever is exposed to a sample in which the target molecule is present, the target molecule will react with the capture molecule on the cantilever
25 surface and a surface stress change will be generated.

Due to the surface stress change of the cantilever, a mechanical compression, stretch or decompression is applied to the cantilever and thereby also to the
30 piezoresistor, and thereby the resistivity of the piezoresistor changes its value. The mechanical compression or decompression may result in a deflection and/or a stretch. By measuring the change in resistance, it can be determined whether the target molecule is
35 present in the sample or not, and if so it may also be possibly to detect the concentration of the target molecule.

Cantilever-based sensors with integrated piezoresistive read-out are described by Thaysen, Ph.D. Thesis, "Cantilever for Bio-Chemical Sensing Integrated in a Microliquid Handling System", September 2001, Microelektronik Centeret, Technical University of Denmark. Hereby the stress changes on the cantilever sensors can be measured directly by the piezoresistor. Moreover, integrated read-out greatly facilitates operation in solutions since the refractive indices of the liquids do not influence the detection as it will using optical read-out. Each sensor may have a built-in reference cantilever, which makes it possible to subtract background drift directly in the measurement. The two cantilevers may be connected in a Whetstone bridge, and the stress change on the measurement cantilever is detected as the output voltage from the Whetstone bridge.

In order to use microcantilevers with integrated piezoresistors for biochemical detection, it is desired to be able to detect very small surface stress changes. The better the surface stress change resolution is, the fewer and weaker molecular interactions can be detected. This is for example important when the detection is used for diagnostic applications, where the molecule of interest is of very low concentration in the sample.

The objective of the present invention is therefore to provide a sensor comprising one or more sensor units with a capture surface, which sensor can be used for detection of the presence of a target in a fluid, such as a biocomponent in a liquid or a gas, with an improved signal, in particular where the molecule of interest is of very low concentration in a liquid sample.

This and other objectives have been achieved by the invention as defined in the claims.

5 **Disclosure of the invention**

The invention is build on the observation by the inventor, that the change in resistance in the piezoresistor of a of prior art sensors is only picked-up
10 in places where the surface stress acts, thus the sensitivity can be considered locally only. This means that the cantilever sensor unit will exhibits constant curvature in places where a surface stress is induced, but be straight and unaffected where no surface stress is
15 obtained. This means that the surface stress only acts locally on the piezoresistor. Therefore the build-in piezoresistive element is only sensitive to local surface stress changes.

20 Based on this observation the inventor found the mechanical amplification principle for the surface stress sensitive sensor unit which forms basis for the present invention

25 In a simple embodiment the sensor according to the invention may consist of two cantilevers one A carrying a capture surface and one B comprising a piezoresistor, which cantilevers are connected in their free end to form a poly-cantilever, e.g. as shown in figure 1. The surface
30 stress acts on cantilever A, and thereby bending it with a constant curvature and thereby constant stress distribution. This will force cantilever B to bend, and since the two cantilevers are connected at the free ends,

cantilever B will experience a point force at the end of the cantilever. The stress increases linearly along the length of the cantilever B. Since the stress level therefore is largest at the base of the cantilever also referred to as its substrate. The piezoresistive element is placed here in order to pick-up the amplified signal.

The sensor of the invention comprises one or more sensor units. The shape and size of the sensor and the size, and the number of sensor units as well as its wiring, may e.g. be as disclosed in any one of the patent applications WO 0066266, DK PA 2001 01724 DK PA 2002 00283, DK PA 2002 00125 and DK PA 2002 00195, which with respect to the disclosure concerning sensor structure and size (not sensor unit structure), materials, wiring, type of capture surface, and fluid chamber structure and size are hereby incorporated by reference.

In the following the sensor is described with one sensor unit, only, but it should be understood that the sensor unit may have several sensor units, such as up to 300, e.g. up to 100.

The sensor unit is in the form of a poly-cantilever structure. By the term poly-cantilever structure means a structure comprising two or more cantilever-like structures, such as 3, 4, or 5 cantilever-like structures. A cantilever-like structure is defined as a structure which is linked to and protrudes from a base also called a substrate. In one embodiment it is desired that the cantilever-like structure is flexible.

The term "flexible" used in relation to the sensor unit means that the sensor unit should be capable of deflecting, e.g. due to stress formed in the surface

stress sensing element or due to amplification using an amplifier.

5 In one embodiment the cantilever-like structure is a structure that protrudes from a substrate and is capable of being deformed (deflected) due to a deformation force of 10^{-3} N or less, such as of 10^{-5} N or less, such as of 10^{-7} N or less, such as of 10^{-9} N or less, such as of 10^{-10} N or less.

10

The poly-cantilever structure comprises two or more cantilever-like structures. The cantilever-like structures is mechanical connected to each other at a distance from their respective substrates. The connection
15 may in one embodiment be a directly connection i.e. the two or more cantilever-like structures are in direct contact with each other. In another embodiment the cantilever-like structures are connected to each other via a connecting element e.g. shaped as a bidge. In this
20 embodiment it is desired that the connecting element should be sufficiently rigid to transfer at least 10 % such as at least 25 %, such as at least 50 % of a deflection from one cantilever-like structures to another cantilever-like structures connected by the connecting
25 element. In one embodiment, the connection element having an average flexibility which is lower than the average flexibility of the piezoresistive cantilever. In one embodiment the connection element is sufficient rigid to remain undeformed when subjected to a force of up to 10^{-10}
30 N. In one embodiment the connection element is sufficient rigid to remain undeformed when subjected to a force of up to 10^{-5} N. In one embodiment the connection element is

sufficient rigid to remain undeformed when subjected to a force of up to 10^{-5} N.

At least one of the cantilever-like structures of a poly-cantilever comprises a piezoresistive element, and at least one of the cantilever-like structures of a poly-cantilever comprises a capture surface.

In the following a cantilever-like structure with a piezoresistive element will also be designated "a piezoresistive cantilever", and a cantilever-like structure with a capture surface will also be designated "a capture surface cantilever".

The cantilever-like structures of a poly-cantilever are connected so that at least one piezoresistive cantilever is connected to at least one capture surface cantilever. The connection is designated "an amplifying connection" which means that a deflection of the capture surface cantilever due to a stress generated at its capture surface is capable of deflecting the connected piezoresistive cantilever.

The cantilever-like structures may in principle have any shape as long as they are linked to each other and that they are relatively flexible as described above. In one embodiment the cantilever-like structures is sheet-formed with an average thickness that is less than both its average length and its average width.

In one embodiment the thickness of the sensor unit is between 0.1 and 25 μm , more preferably between 0.3 and 5 μm , such as about 1 μm . The other dimensional parameters, thickness, width and or diameter, may preferably be up to

about 500 μm , more preferably up to about 100 μm , such as about 50 μm .

In one embodiment, the respective cantilever-like structures has an average thickness of at least 5 times, preferably at least 50 times less than its average width, and/or the respective cantilever-like structures has an average thickness of at least 5 times, preferably at least 50 times less than its average length. As the cantilever-like structures in one embodiment may have shapes with no unambiguous definition of width and length, e.g. rounded or circular shapes, it is in this embodiment preferred that such cantilever-like structure has an average thickness of at least 5 times, preferably at least 50 times less than its other dimensions including width, length and diameter.

In one embodiment the respective cantilever-like structures being in the form of a sheet formed unit linked to a substrate and protruding there from. The periphery of the cantilever-like structure is determined as the line along the cantilever edge, the connection line to the substrate and the one or more connection lines to other cantilever-like structures. The connection lines are determined as straight lines. The periphery of the cantilever-like structures may be regular or irregular. In one embodiment the periphery of the cantilever-like structure is independently from each other selected between square formed, rectangular, triangular, pentagonal, hexagonal, leaf shaped, circular and oval periphery.

As mentioned above, a connection line between to cantilever-like structures is determined as a straight

line. In some structures an exact connection line between two cantilever-like structures is not simple to determine because the cantilever-like structures at the area of the connection comprise a protuberance. In such situation the
5 cantilever connection line is determined as the shortest line through the protuberance. In case there is an area where a line through the protuberance can be shortest so that several lines of equal shortest length could be made i.e. an area where the protuberance is narrowest, the
10 cantilever connection line is a midline through the protuberance at the area where it is narrowest.

In some structures an exact connection line between two cantilever-like structures is not simple to determine
15 because the cantilever-like structures are "overlapping" or are "grown" into each other. In such situation the cantilever connection line is determined as the shortest line between the cantilever-like structures.

20 In one embodiment the poly-cantilever structure comprises two, three or four cantilever-like structures, the cantilever-like structures preferably having equal shape.

The cantilever-like structures of a poly-cantilever may
25 be linked to the same substrate or to different substrates. The cantilever-like structures may be linked to the substrate by being integrated to each other or by a connection means e.g. a glue or a click lock. In one embodiment the cantilever-like structure and the
30 substrate are produced separately of each other, at least one of the cantilever-like structure and the substrate comprise a thermoplastic, the cantilever-like structure and the substrate being held together and heated to thereby fixate the cantilever-like structures to the substrate.

Similarly the cantilever-like structures may be connected to each other after their production.

5 In one embodiment the cantilever-like structures and the substrate are produced as a single unit i.e. integrated with each other. In this embodiment it is often desired that the basic material of the cantilever-like structures is also the basic material of the substrate. The term "basic material" means the major part by volume of the
10 material exclusive the material of the capture coating, the piezoresistive element and the wiring.

The connection between a cantilever-like structure and its substrate may be identified according to its material
15 thickness i.e. the substrate is more rigid than the cantilever-like structure, e.g. more than 3, 5 or 10 times as rigid as the sensor unit. The substrate may e.g. be thicker than the cantilever-like structure, e.g. more than 3, 5, 10 or 25 times as thick as the cantilever-like
20 structure.

As mentioned above the connection line between a cantilever-like structure and its substrate, is determined as a straight line. This means in practice
25 that the connection line is determined by following the edge of the cantilever-like structure until a first connection point to the substrate, determining the second connection point by following the true connection, and drawing a straight line between the two points.

30 The %-vice connection distance of a connection between two cantilever-like structures to their respective substrates being determined individually for each cantilever-like structure. The %-vice connection distance
35 of a connection of a first cantilever-like structure to

another also designated a cantilever connection line and the substrate linked to said first cantilever-like structure, is determined as the shortest distance between the cantilever connection line and the substrate connection line. The % -vice distance being in % of the total length of the protruding first cantilever-like structure. The length of the cantilever-like structure is determined as the longest distance from the remotest part of the cantilever-like structure to the middle of the substrate connection line.

In one embodiment the two or more cantilever-like structures of a poly-cantilever structure are connected to each other at a connection distance for one or preferably both cantilever-like structures which is 50 % or more, such as 70 % or more, Such as 90 % or more.

In one embodiment the cantilever-like structures is connected to each other at a connection line with a connection distance for both cantilever-like structures which is 95 % or more. This is referred to as being their free end. In case of a traditional rectangular cantilever the fee end includes the edge which is farthest away from the substrate to which it is linked.

In one embodiment the connection between the cantilever-like structures being in the form of a joining along a length section of the periphery of at least one of the cantilever-like structures, i.e. a section of the periphery which do not include the free ends of at least one of the cantilever-like structures.

In one embodiment the poly-cantilever structure has an essentially rectangular or square formed periphery. The two or more cantilever-like structures of the poly-

cantilever structure are connected to each other at their free edge, wherein the free edge of the cantilever is the edge which is farthest away from the substrate, to which it is linked. The piezoresistive cantilever is preferably
5 connected to the one or more other cantilever-like structures along 60 % or less, such as 40 % or less, such as 20 % or less of the length of the free edge of the piezoresistive cantilever. In one embodiment the connection e.g. via a connection element is located to at
10 least cover the median of the free edge line.

The cantilever-like structures may in one embodiment be placed parallel to each other. This means in practice that the protruding directions are parallel. The
15 protruding direction of a cantilever-like structure is determined as the direction measured from the median of the substrate connection line to the remotest part of the cantilever-like structure.

20 In one embodiment the cantilever-like structure of the poly-cantilever structure protrudes in directions from their respective substrates which directions has/have an angle or angles to each other which is/are within the interval 0 to 45°, preferably the directions has/have an
25 angle or angles to each other which is/are within the interval 0 to 15°.

As described above it is in one embodiment desired that the cantilever-like structures has a high flexibility. In
30 this connection it can further be added that in general the lower force necessary to deflect the piezoresistive cantilever, the higher is its sensitivity.

The flexibility of the respective cantilever-like structure may in one embodiment be equal over its extension from the substrate connection line and towards its free end.

5

In one embodiment the flexibility of the piezoresistive cantilever is varying over its extension from the substrate line and towards its free end, the flexibility preferably being highest at a distance from the substrate which is 50 % or less, such as 30 % or less of the length of the protruding cantilever.

The piezoresistive element is normally partly integrated or protrudes into the substrate where it is connected to two wires. The piezoresistive element may in one embodiment have an extension into the piezoresistive cantilever to a distance from the substrate connection line which is 80 % or less, such as 50 % or less, such as 30 % or less of the length of the protruding cantilever. By providing the piezoresistive cantilever with a high flexibility in areas of the cantilever where it contains the piezoresistive element, an increased signal may be obtained.

The sensitivity of the sensor with a sensor unit as described above is in general relatively high compared to prior art sensors, since the stress generated on one surface area and resulting in a deflection, can be transferred to another cantilever-like structure in the form of the deflection. In one embodiment the capture surface cantilever has a larger surface area than the piezoresistive cantilever, thereby a high deflection can

be detected particular when concentrations of a target substance in a liquid or gas is low.

5 In one embodiment of the sensor according to the invention the surface stress change acting on a capture surface cantilever can be concentrated to act on a small part of the piezoresistive cantilever. For example if a surface stress of 1 N/m is acting on a cantilever area of 1000 μm^2 , this may be concentrated down to act on an area
10 of 10 μm^2 . Thereby the stress change in that area would be 100 N/m and thereby increasing the sensitivity 100 times.

15 In one embodiment the poly-cantilever comprises two or more capture surface cantilevers, thereby an even higher signal may be obtained.

In one embodiment the piezoresistive cantilever also comprises a capture surface. The piezoresistive element
20 may in such circumstances be insulated in particular if the sensor is designed for use in detecting of a target substance in a liquid. The insulation of the piezoresistive element may e.g. be as described in WO 0066266.

25 In one embodiment where the piezoresistive cantilever do not comprise a capture surface, the piezoresistive element need not be insulated even if used in detecting of a target substance in a liquid, because the
30 piezoresistive cantilever do not need to come into contact with the liquid. Thereby the sensor may be much more simple to produce because steps of insulating the piezoresistive element may be omitted.

The cantilever-like structures as well as the substrate may e.g. be from materials selected from silicon, silicon oxide, silicon nitride, metals, polymers, glass compositions, ceramics, plastics or any combinations of these materials.

The group of polymers preferably includes epoxy resin, polystyrene, polyethylene, polyvinylacetate, polyvinylchloride, polyvinylpyrrolidone, polyacrylonitrile, polymethylmetacrylate, polytetrafluoroethylene, polycarbonate, poly-4-methylpentylene, polyester, polypropylene, cellulose, nitrocellulose, starch, polysaccharides, natural rubber, butyl rubber, styrene butadiene rubber and silicon rubber.

In order to have optimal processability, the substrate should preferably be of or comprise a material which can act as a photo resistor. Preferred materials include an epoxy resin, preferably selected from the group consisting of epoxy functional resin having at least two epoxy groups, preferably an octafunctional epoxidized novalac. Particularly preferred materials are described in US 4882245 which is hereby incorporated by reference. The most preferred material is the octafunctional epoxidized novalac which is commercially available from Celanese Resins, Shell Chemical, MicroChem Inc under the tradename SU-8, and from Softec Microsystems under the tradename SM10#0.

For applications in liquid, the wires need to be insulated, and the substrate should therefore preferably consist of or comprise an electrically insulating

material, which prevents short-circuiting of the electrical connections during operation. The insulating material could e.g. be a polymer, silicon nitride, silicon oxide, metal oxides, etc. In case the electrical connection line includes doped silicon, the insulating property can be obtained by reversed biased diode effect. For a wire consisting of p-type silicon, the reversed biased diode effect is obtained by encapsulating the wire in n-type silicon.

10

The sensor according to the invention includes an electric communication line for applying a voltage over the piezoresistive element. The electric communication line includes a pair of wires connected to the piezoresistive element. The wires may be of the same material as the piezoresistive element. In the situation where the wires and the piezoresistor are of the same material, the piezoresistor will preferably be thinner, e.g. a thinner layer or a smaller wire diameter. In other situations the wires and the piezoresistor are of different materials and are fixed to each other at a connection point e.g. by welding. The method of connecting wires to a piezoresistive element is generally known in the art, and reference is made to the prior art referred to above. The electric communication line may consist of the wires, but it may also include other elements such as diodes, other resistors, e.g. a part of a Whetstone bridge.

30 In one embodiment the wires are integrated in the substrate and insulated as described above.